

**AMENDMENTS TO THE CLAIMS**

1. (Currently Amended) A method of manufacturing a solid-state imaging device comprising the steps of:

forming a plurality of IT-CCDs on a surface of a semiconductor substrate;

bonding a translucent member to the surface of the semiconductor substrate in order to have a gap opposite to each light receiving region of the IT-CCD;

forming an external connecting terminal corresponding to the IT-CCD; and

isolating a bonded member obtained at the bonding step and provided with the external connecting terminal for each of the IT-CCDs, and the isolating step includes separating the translucent member to position a peripheral edge portion of the translucent member onto an inside of a peripheral edge portion of the IT-CCD in such a manner that a surface of the peripheral edge portion of the IT-CCD is exposed away from the translucent member, wherein the external connecting terminal is exposed away from the bonded member.

2. (Original) The method of manufacturing a solid-state imaging device according to Claim 1, wherein the step of bonding a translucent member includes the steps of:

preparing a translucent substrate having a concave portion in a position corresponding to a region in which the IT-CCD is to be formed; and

bonding the translucent substrate to the surface of the semiconductor substrate.

3. (Previously Presented) A method of manufacturing a solid-state imaging device comprising the steps of:

forming a plurality of IT-CCDs on a surface of a semiconductor substrate;

selectively removing the surface of the semiconductor substrate to surround a light receiving region, thereby forming a protruded portion, a gap being formed between the light receiving region and a translucent member by the protruded portion

bonding the translucent member to the surface of the semiconductor substrate in order to have a gap opposite to each light receiving region of the IT-CCD;

forming an external connecting terminal corresponding to the IT-CCD; and

isolating a bonded member obtained at the bonding step and provided with the external connecting terminal for each of the IT-CCDs.

4. (Currently Amended) ~~[[The]]~~ A method of manufacturing a solid-state imaging device ~~according to Claim 1[[,]]~~ comprising the steps of:

forming a plurality of IT-CCDs on a surface of a semiconductor substrate;

~~wherein prior to the bonding step, the method further comprises~~ selectively removing ~~[[the]]~~ a surface of ~~[[the]]~~ a translucent member to surround a light receiving region, thereby forming a ~~spacer, and~~ spacer;

bonding the translucent member to the surface of the semiconductor substrate in order to have a gap opposite to each light receiving region of the IT-CCD so that  
~~wherein at the bonding step[[,]]~~ a gap is formed between the semiconductor substrate

and the translucent member through the spacer provided to surround the light receiving region;

forming an external connecting terminal corresponding to the IT-CCD; and  
isolating a bonded member obtained at the bonding step and provided with the  
external connecting terminal for each of the IT-CCDs, wherein the external connecting  
terminal is exposed away from the bonded member.

5. (Currently Amended) The method of manufacturing a solid-state imaging device according to any of Claims ~~1 to 4~~ 3 or 4, wherein the isolating step includes the step of separating the translucent member to position a peripheral edge portion of the translucent member onto an inside of a peripheral edge portion of the IT-CCD in such a manner that ~~the~~ the surface of a peripheral edge portion of the IT-CCD is exposed away from the translucent member.

6. (Previously Presented) The method of manufacturing a solid-state imaging device according to Claim 3, wherein said step of bonding is performed at a temperature under 80 degrees C.

7. (Original) The method of manufacturing a solid-state imaging device according to Claim 6, wherein, in the bonding step, a room temperature setting adhesive is utilized for bonding the translucent member to the surface of the semiconductor substrate.

8. (Original) The method of manufacturing a solid-state imaging device according to Claim 6, wherein, in the bonding step, a photo-curing adhesive is utilized for bonding the translucent member to the surface of the semiconductor substrate.

9. (Original) The method of manufacturing a solid-state imaging device according to Claim 1 or Claim 2, prior to said step of isolating, further comprising the step of:

resin shielding for shielding the translucent member in vicinity of the bonding link with the surface of the semiconductor substrate by a resin so that the external connecting terminal is exposed.

10. (Currently Amended) The method of manufacturing a solid-state imaging device according to ~~Claim 3~~ Claim 9, wherein the resin shielding step is performed at a temperature under 80 degree degrees C.

11-49. (Cancelled)